



RECTRON

SEMICONDUCTOR

TECHNICAL SPECIFICATION

LS4148

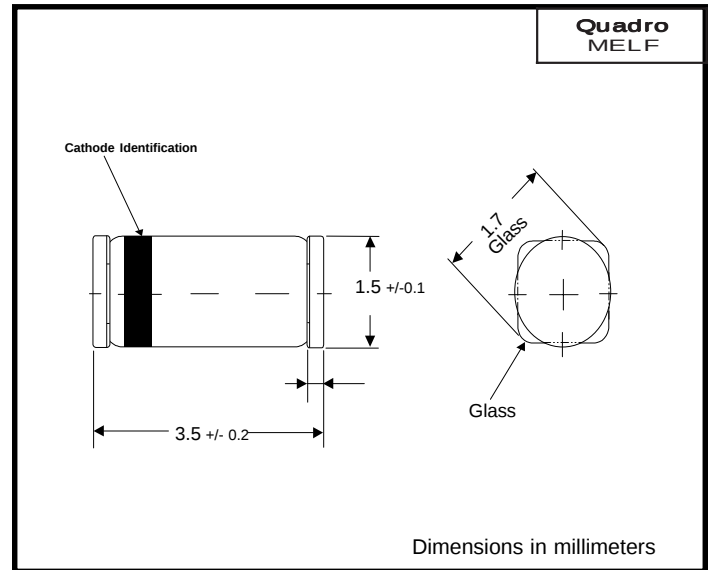
1N4148 Quadro MELF SIGNAL DIODE

Absolute Maximum Ratings (Ta=25°C)

Items	Symbol	Ratings	Unit
Reverse Voltage	VR	75	V
Reverse Recovery Time	trr	4	ns
Power Dissipation 3.33mW/°C (25°C)	P	500	mW
Forward Current	IF	150	mA
Junction Temp.	Tj	-65 to 175	°C
Storage Temp.	Tstg	-65 to 175	°C

Mechanical Data

Items	Materials
Package	QUADRO MELF
Case	Hermetically sealed glass
Lead/Finish	Double stud/Solder Plating
Chip	Glass Passivated



Electrical Characteristics (Ta=25°C)

Ratings	Symbol	Ratings	Unit
Minimum Breakdown Voltage @IR= 100uA	BV	100	V
Peak Forward Surge Current tp= 1μsec.	IFsurge	2	A
Maximum Forward Voltage IF= 10mA	VF	1.0	V
Maximum Reverse Current VR= 20V VR= 75V VR= 20V, Tj= 150°C	IR	0.025 5.0 50	uA
Maximum Junction Capacitance VR= 0, f= 1 MHz	Cj	4	pF
Maximum Reverse Recovery Time IF= 10mA, VR= 6V, IRR= 1mA, RL= 100Ω	trr	4	ns
Maximum Thermal Resistance (on PC Board 50mm x 50mm x 1.6mm)	RθJA	500	°C/W
Maximum Rectification Efficiency Vrf= 2V, f= 100MHz	ηv	0.45	%

RECTRON USA

1315 John Reed Court, Industry, CA 91745
Tel: (626) 333-3802 Fax: (626) 330-6296 www.rectron.com